

ST2408HI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

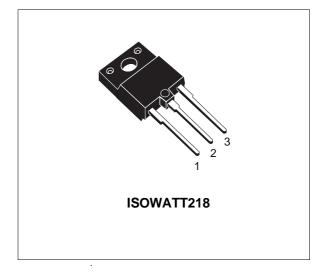
- NEW SERIES, ENHANCED PERFORMANCE
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- HIGH VOLTÁGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

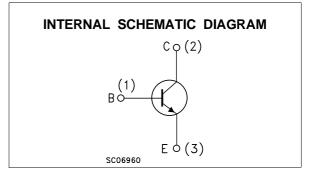
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR MONITORS 17 INCHES AND HIGH END TVS

DESCRIPTION

The device is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0)	1500	V
VCEO	Collector-Emitter Voltage $(I_B = 0)$	600	V
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$	7	V
lc	Collector Current	12	А
I _{CM}	Collector Peak Current (t _p < 5 ms)	25	А
IB	Base Current	7	А
P _{tot}	Total Dissipation at $T_C = 25 \ ^{\circ}C$	55	W
V _{isol}	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

THERMAL DATA

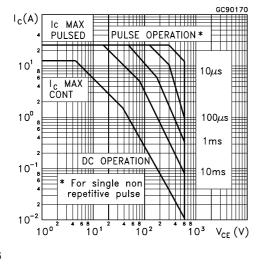
R _{thj-case}	Thermal Resistance Junction-case	Max	2.3	°C/W	
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

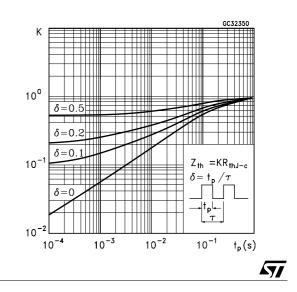
Symbol	Parameter	Test C	onditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V				1	mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 7 V				1	mA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	L = 25 mH	600			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 8 A	I _B = 2 A			3	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 8 A	I _B = 2 A			1.5	V
h _{FE} *	DC Current Gain	$I_{C} = 1 A$ $I_{C} = 5 A$ $I_{C} = 8 A$	V _{CE} = 5 V V _{CE} = 1 V V _{CE} = 5 V	6	25 5.5	9	
ts t _f	INDUCTIVE LOAD Storage Time Fall Time	$ I_{C} = 6 \text{ A} \\ I_{B(on)} = 950 \text{ mA} \\ L_{BB(off)} = 1.5 \mu\text{H} $	$\label{eq:hb} \begin{array}{l} f_h = 64 \ \text{KHz} \\ V_{\text{BB(off)}} = -2.5 \ \text{V} \\ \text{(see figure 1)} \end{array}$		2.5 110	3 260	μs ns

 \ast Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %

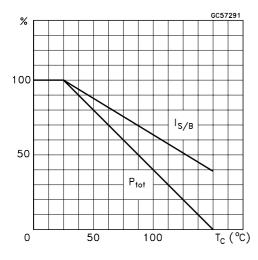
Safe Operating Area



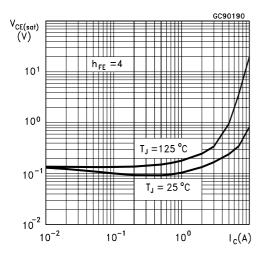
Thermal Impedance



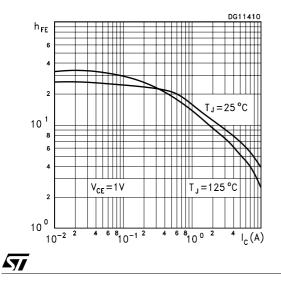
Derating Curve



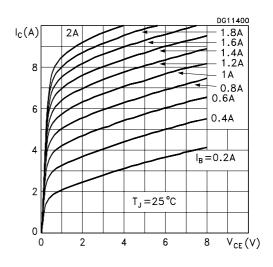
Collector Emitter Saturation Voltage



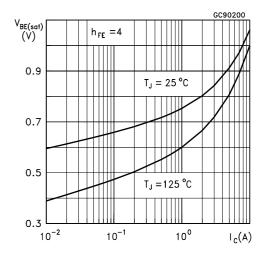
DC Current Gain



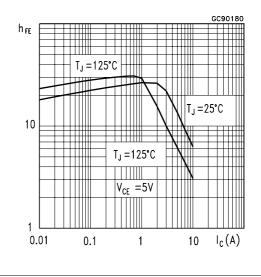
Output Characteristics



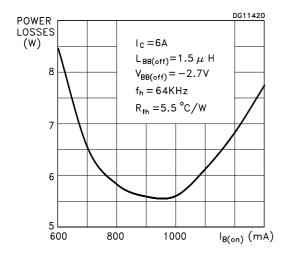
Base Emitter Saturation Voltage



DC Current Gain



Power Losses



Reverse Biased Soa

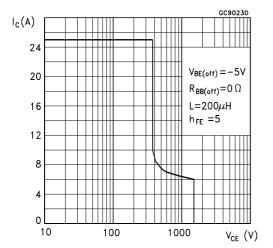
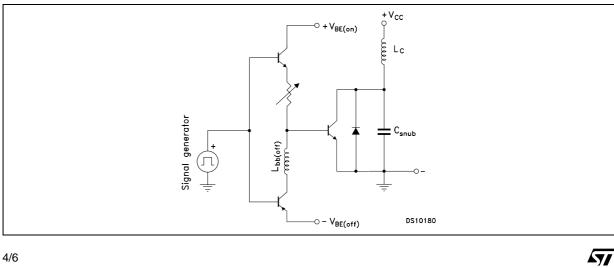
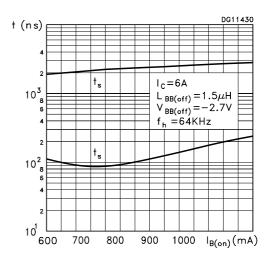


Figure 1: Inductive Load Switching Test Circuit.

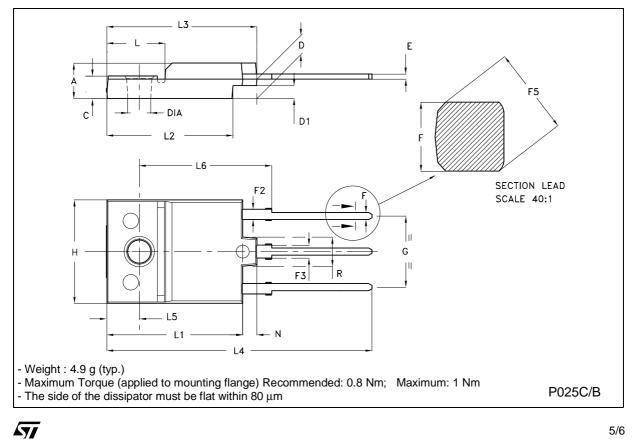


Switching Time Inductive Load



DIM.	mm		inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	5.35		5.65	0.211		0.222
С	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	0.75		0.95	0.030		0.037
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
F5			1.10			0.043
G	10.80		11.20	0.425		0.441
Н	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
Ν	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146

ISOWATT218 NARROW LEADS MECHANICAL DATA



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